

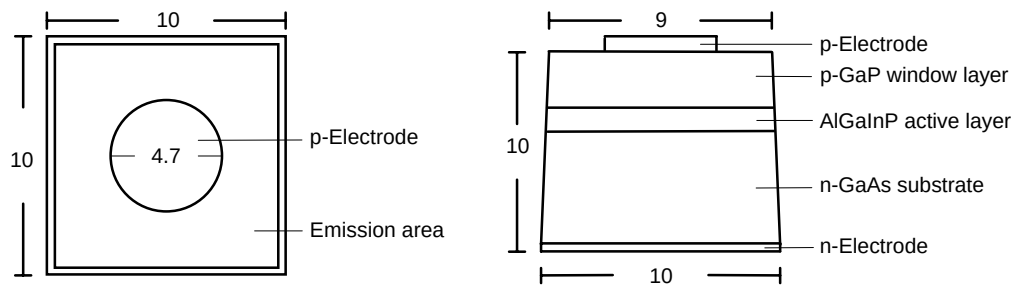
■ Features :

- HP MOVPE epi wafer
- Low VF and superior thermal stability
- High light output at four sides results high total light output and wide view angle after packaging
- High reliability

■ Typical Applications :

- Traffic Signal Modules: Pedestrian Signs
- Advertising Signs and Marquees
- Industrial Products

■ Outline Dimensions : (Unit: mil)



■ Physical Structure :

Chip dimension	Chip size	10.0 mils x 10.0 mils
	Thickness	10.0 mils
	Emission area	9.0 mils
	Bonding pad	4.7 mils
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Not frosted	

■ Electro-Optical Characteristics : (Ta = 25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	1.90	2.20	V
Reverse Voltage	V_R	$I_R = 10 \mu\text{A}$	5	-	-	V
Wavelength	λ_D	$I_F = 20 \text{ mA}$	-	605	-	nm
	Hue		596	602	611	
Spectral width at half height	$\Delta\lambda$	$I_F = 20 \text{ mA}$	-	18	-	nm
Luminous Intensity	I_v	$I_F = 20 \text{ mA}$	C1	35	-	mcd
			D1	45	-	
			E1	65	-	
			F1	75	-	

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

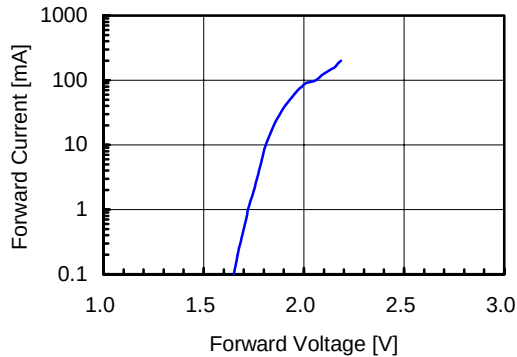


Fig 2. Relative Intensity vs. Forward Current

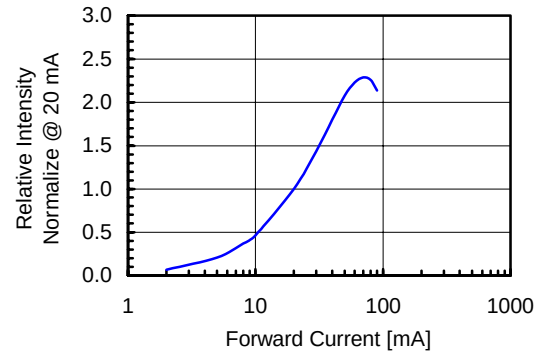


Fig 3. Forward Voltage vs. Temperature

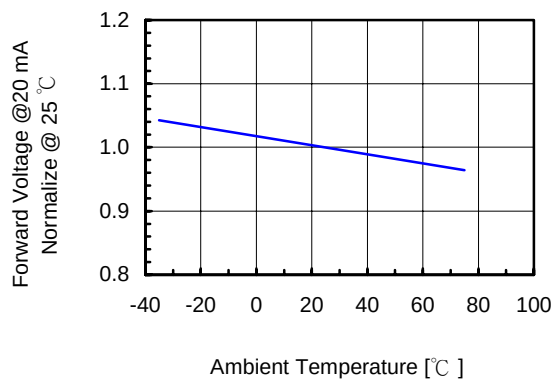


Fig 4. Relative Intensity vs. Temperature

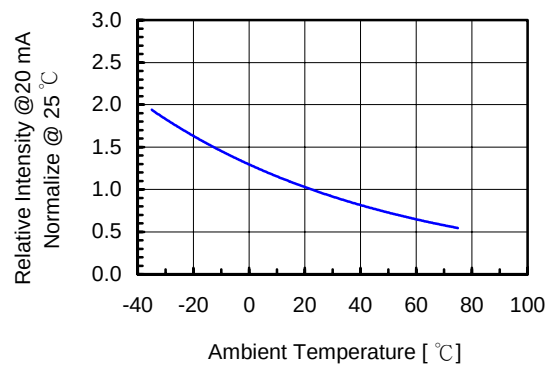
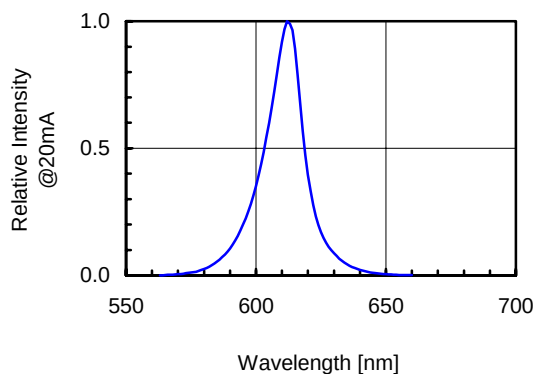


Fig 5. Relative Intensity vs. Wavelength



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